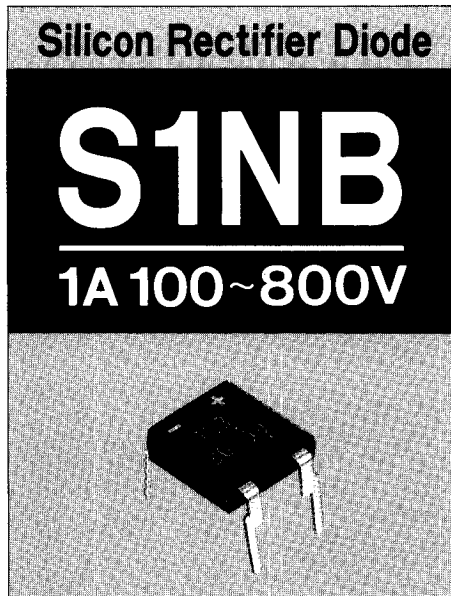
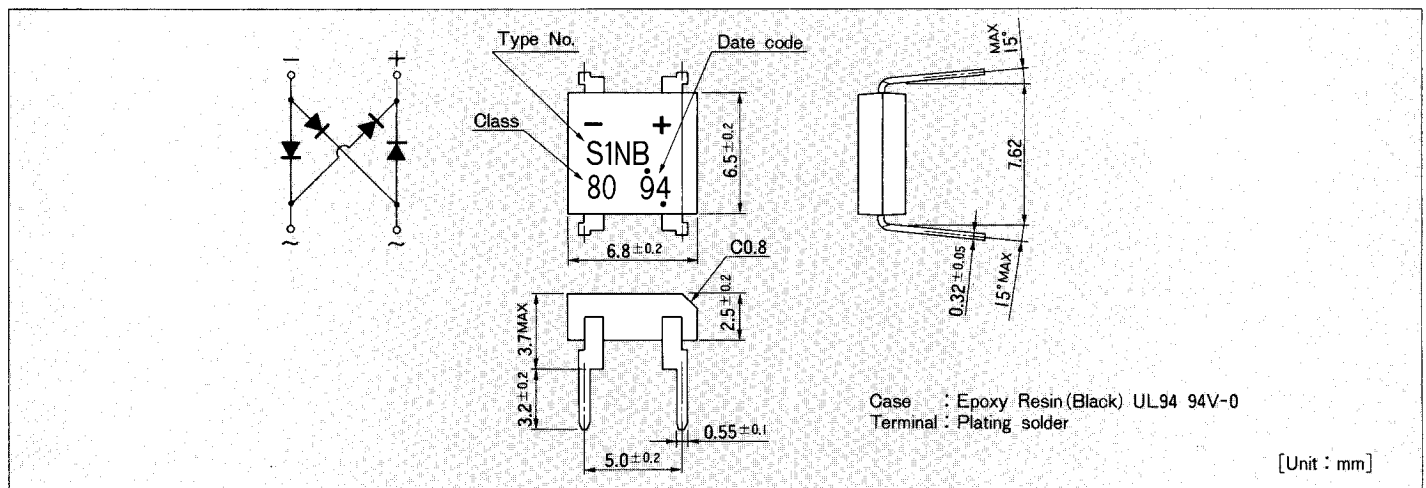




THE ADVANCED 1 AMPERE RECTIFIER DIODES ON THE MARKET TODAY

**Compact And Lightweight Construction With
Superior Current Characteristics.**

OUTLINE DIMENSIONS



FEATURES

- Glass passivated chip.
- Smallest size and lightest weight 1 Amp. rated bridge diodes.
- Stick packages are available for automated assembly machine.

RATINGS

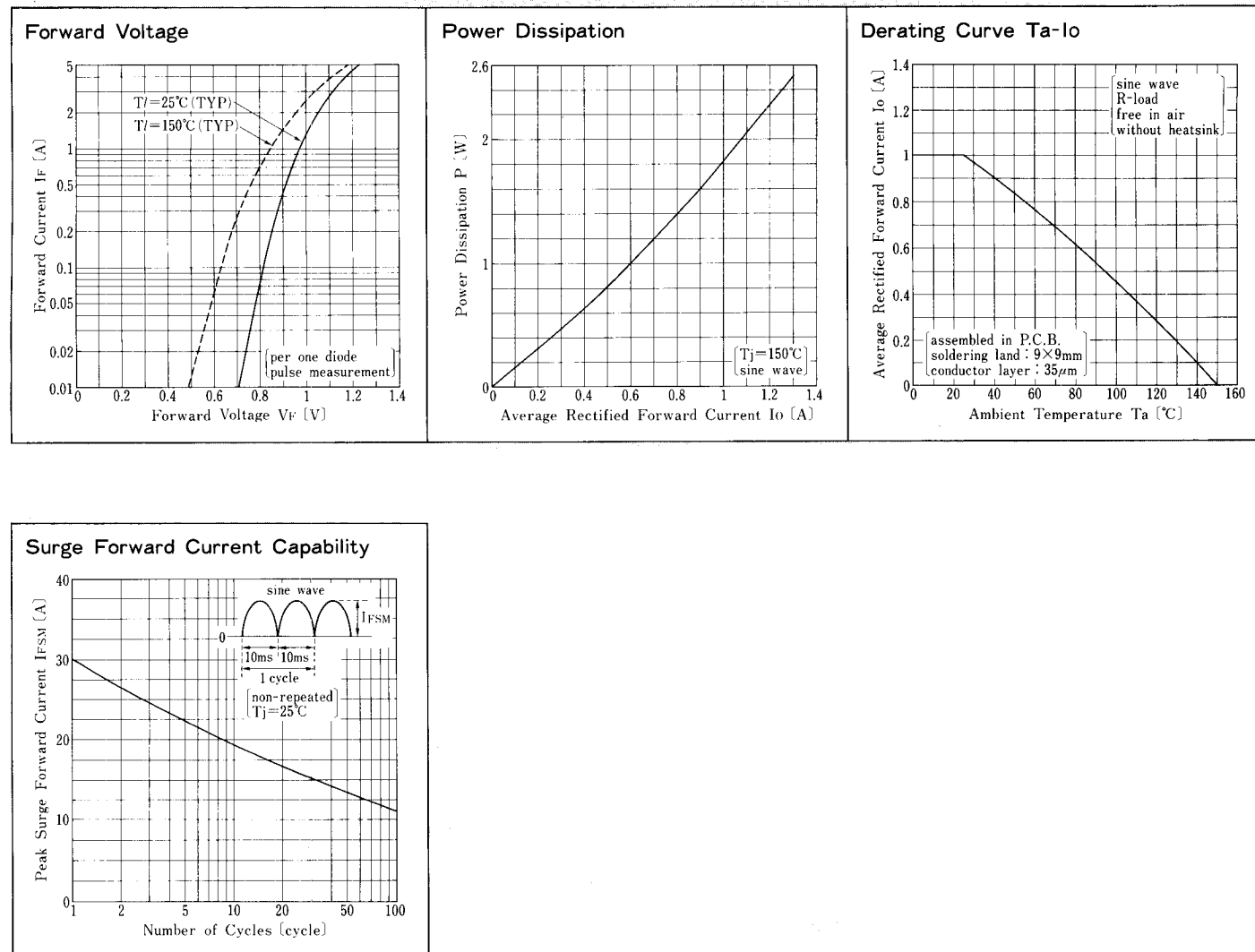
Absolute Maximum Ratings

Item	Symbol	Conditions	Type No.	S1NB 10	S1NB 20	S1NB 40	S1NB 60	S1NB 80	Unit
Storage Temperature	T _{stg}			-40~150					°C
Operating Junction Temperature	T _j			150					°C
Maximum Reverse Voltage	V _{RM}			100	200	400	600	800	V
Average Rectified Forward Current	I _o	50Hz sine wave, Resistive load, T _a =25°C, On P.C.B.		1					A
Peak Surge Forward Current	I _{FSM}	50Hz sine wave, Non-repetitive 1 cycle peak value, T _j =25°C		30					A

Electrical Characteristics (T_j=25°C)

Forward Voltage	V _F	I _F =0.5A, Pulse measurement, Rating of per diode	MAX	1.05		V
Reverse Current	I _R	V _R =V _{RM} , Pulse measurement, Rating of per diode	MAX	10	MAX 20	μA
Thermal Resistance	θ _{jl}	Between junction and lead	MAX	15		°C/W
	θ _{ja}	Between junction and ambient	MAX	68		

CHARACTERISTIC DIAGRAMS



● Note : All specifications are subject to change without notice.

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